Analog Power AM3428N

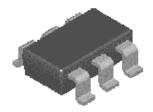
## N-Channel 20V (D-S) MOSFET

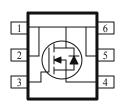
These miniature surface mount MOSFETs utilize High Cell Density process. Low  $r_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are power switch, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low r <sub>DS(on)</sub> Provides Higher Efficiency and
	Extends Battery Life

- Low Gate Charge
- Fast Switch
- Miniature TSOP-6 Surface Mount Package Saves Board Space

PRODUCT SUMMARY				
$V_{\mathrm{DS}}\left(\mathrm{V}\right) = r_{\mathrm{DS}\left(\mathrm{on}\right)}\left(\Omega\right) = I_{\mathrm{D}}\left(\mathrm{A}\right)$				
20	$0.025$ @ $V_{GS} = 4.5 \text{ V}$	7.4		
20	$0.035$ @ $V_{GS} = 2.5V$	6.2		





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			Maximum	Units		
Drain-Source Voltage			20	V		
Gate-Source Voltage			±8	V		
C ( D C (a	$T_A=25^{\circ}C$	] <sub>T_</sub>	7.4			
Continuous Drain Current <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	1D	6.0	A		
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	±20				
Continuous Source Current (Diode Conduction) <sup>a</sup>			1.6	A		
D	$T_A=25^{\circ}C$	D	2.0	W		
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	rD	1.3	VV		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Manipulation 4. April 1948	t <= 5 sec	p	62.5	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	$\kappa_{ m THJA}$	110	C/W		

1

## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM3428N

Davamatan	Symbol	Total Constitution		Limits	3	TT *4
Parameter	Symbol Test Conditions		Min	Тур	Max	Unit
Static						
Gate-Threshold Voltage	VGS(th)	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	0.7			V
Gate-Body Leakage	Igss	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			±100	nA
Zero Gate Voltage Drain Current	Idss	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zelo Cate Voltage Diam Current	IDSS	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			A
Drain-Source On-Resistance <sup>A</sup>	fDS(on)	$V_{GS} = 4.5 \text{ V}, I_D = 7.4 \text{ A}$	2		25	mΩ
		$V_{GS} = 2.5 \text{ V}, I_D = 6.2 \text{ A}$			35	1112
Forward Tranconductance <sup>A</sup>	gs	$V_{DS} = 10 \text{ V}, I_D = 4.0 \text{ A}$		11.3		S
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 1.6 A, V_{GS} = 0 V$		0.75		V
Dynamic <sup>b</sup>						
Total Gate Charge	Qg			13.4		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 7.4 \text{ A}$		0.9		nC
Gate-Drain Charge	Qgd			2.0		
Turn-On Delay Time	t <sub>d(on)</sub>			8		
Rise Time	$t_{\rm r}$	$V_{DD} = 10 \text{ V}, R_L = 15 \Omega, I_D = 1 \text{ A},$		24		
Turn-Off Delay Time	td(off)	$V_{GEN} = 4.5 \text{ V}$		35		ns
Fall-Time	tf			10		

## Notes

a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .

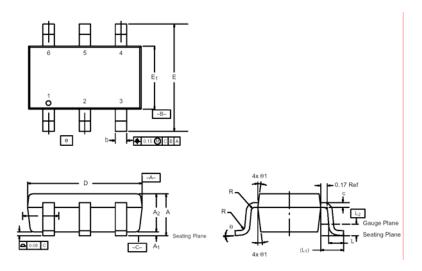
b. Guaranteed by design, not subject to production testing.

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Analog Power AM3428N

## Package Information

TSOP-6: 6LEAD



	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	_	0.043
A <sub>1</sub>	0.01	_	0.10	0.0004	-	0.004
A <sub>2</sub>	0.84	_	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
е		1.00 BSC 0.0394 BSC			;	
L	0.35	_	0.50	0.014	ı	0.020
L <sub>1</sub>	0.60 Ref				0.024 Ref	
L <sub>2</sub>	0.25 BSC				0.010 BSC	
R	0.10	_	-	0.004	_	_
θ	0°	4°	8°	0°	4°	8°
$\theta_1$	7° Nom 7° Nom					

3